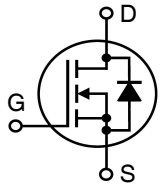
IXYS

Q3-Class HiperFET™ Power MOSFET

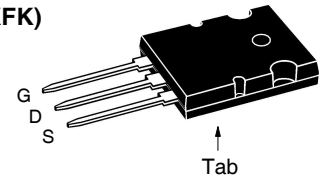
IXFK32N100Q3
IXFX32N100Q3

V_{DSS} = 1000V
I_{D25} = 32A
$R_{DS(on)}$ ≤ 320mΩ
t_{rr} ≤ 300ns

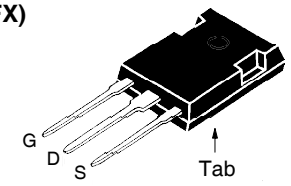
N-Channel Enhancement Mode
Fast Intrinsic Rectifier



TO-264 (IXFK)



PLUS247 (IXFX)



G = Gate D = Drain
S = Source Tab = Drain

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	T_J = 25°C to 150°C	1000	V
V_{DGR}	T_J = 25°C to 150°C, R_{GS} = 1MΩ	1000	V
V_{GSS}	Continuous	±30	V
V_{GSM}	Transient	±40	V
I_{D25}	T_C = 25°C	32	A
I_{DM}	T_C = 25°C, Pulse Width Limited by T_{JM}	96	A
I_A	T_C = 25°C	32	A
E_{AS}	T_C = 25°C	2	J
dv/dt	$I_S \le I_{DM}$, $V_{DD} \le V_{DSS}$, $T_J \le 150°C$	50	V/ns
P_D	T_C = 25°C	1250	W
T_J		-55 ... +150	°C
T_{JM}		150	°C
T_{stg}		-55 ... +150	°C
	Maximum Lead Temperature for Soldering	300	°C
T_{SOLD}	Plastic Body for 10s	260	°C
M_d	Mounting Torque (TO-264)	1.13/10	Nm/lb.in.
F_C	Mounting Force (PLUS247)	20..120 /4.5..27	N/lb.
Weight	TO-264	10	g
	PLUS247	6	g

Symbol	Test Conditions (T_J = 25°C Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
BV_{DSS}	V_{GS} = 0V, I_D = 3mA	1000			V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, I_D = 8mA	3.5		6.5	V
I_{GSS}	V_{GS} = ±30V, V_{DS} = 0V			±200	nA
I_{DSS}	$V_{DS} = V_{DSS}$, V_{GS} = 0V			50	μA
	T_J = 125°C			3	mA
$R_{DS(on)}$	V_{GS} = 10V, $I_D = 0.5 \bullet I_{D25}$, Note 1			320	mΩ

Features

- International Standard Packages
- Low Intrinsic Gate Resistance
- Avalanche Rated
- Low Package Inductance
- Fast Intrinsic Rectifier
- Low $R_{DS(on)}$ and Q_G

Advantages

- High Power Density
- Easy to Mount
- Space Savings

Applications

- DC-DC Converters
- Battery Chargers
- Switch-Mode and Resonant-Mode Power Supplies
- DC Choppers
- Temperature and Lighting Controls

© 2020 IXYS CORPORATION, All Rights Reserved

Symbol	Test Conditions (T_J = 25°C Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
g_{fs}	V_{DS} = 20V, I_D = 0.5 • I_{D25}, Note 1	20	32		S
C_{iss}	V_{GS} = 0V, V_{DS} = 25V, f = 1MHz		10990		pF
C_{oss}			745		pF
C_{rss}			67		pF
R_{Gi}	Gate Input Resistance		0.20		Ω
$t_{d(on)}$	**Resistive Switching Times**		45		ns
t_r	V_{GS} = 10V, V_{DS} = 0.5 • V_{DSS}, I_D = 0.5 • I_{D25}		15		ns
$t_{d(off)}$	R_G = 1Ω (External)		54		ns
t_f			12		ns
$Q_{g(on)}$	V_{GS} = 10V, V_{DS} = 0.5 • V_{DSS}, I_D = 0.5 • I_{D25}		195		nC
Q_{gs}			60		nC
Q_{gd}			78		nC
R_{thJC}				0.10	°C/W
R_{thCS}			0.15		°C/W

Source-Drain Diode

Symbol	Test Conditions (T_J = 25°C Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
I_S	V_{GS} = 0V			32	A
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			128	A
V_{SD}	I_F = I_S, V_{GS} = 0V, Note 1			1.4	V
t_{rr}	I_F = 16A, -di/dt = 100A/μs			300	ns
Q_{RM}	V_R = 100V, V_{GS} = 0V		1.2		μC
I_{RM}			12.3		A

Note 1. Pulse test, t ≤ 300μs, duty cycle, d ≤ 2%.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,860,072 4,881,106 4,931,844 5,017,508 5,034,796 5,049,961 5,063,307 5,187,117 5,237,481 5,381,025 5,486,715 6,162,665 6,259,123 B1 6,306,728 B1 6,404,065 B1 6,534,343 6,583,505 6,683,344 6,710,405 B2 6,710,463 6,727,585 6,759,692 6,771,478 B2 7,005,734 B2 7,063,975 B2 7,071,537 7,157,338B2

Fig. 1. Output Characteristics @ T_J = 25°C

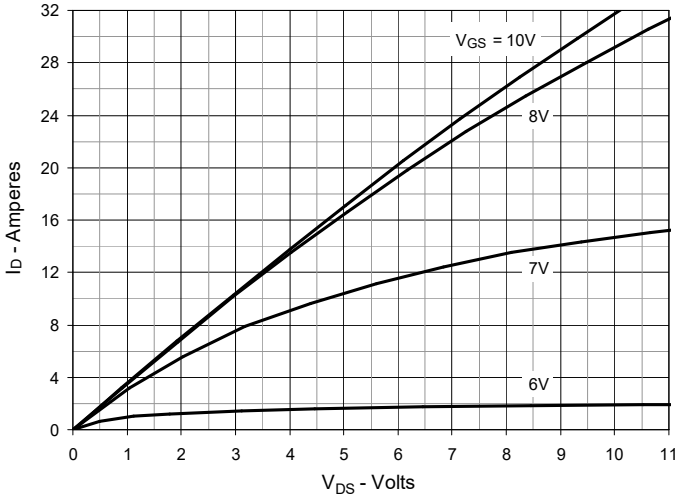


Fig. 2. Extended Output Characteristics @ T_J = 25°C

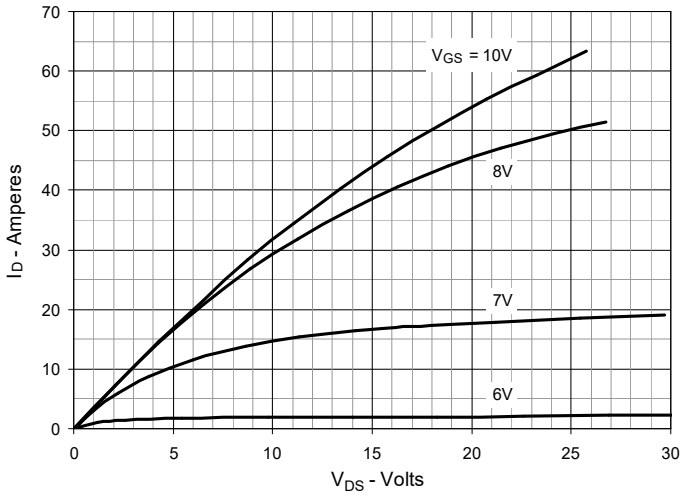


Fig. 3. Output Characteristics @ T_J = 125°C

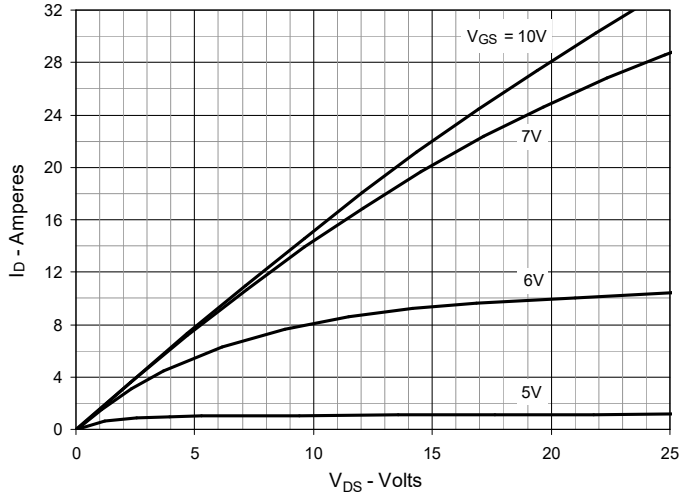


Fig. 4. $R_{DS(on)}$ Normalized to I_D = 16A Value vs. Junction Temperature

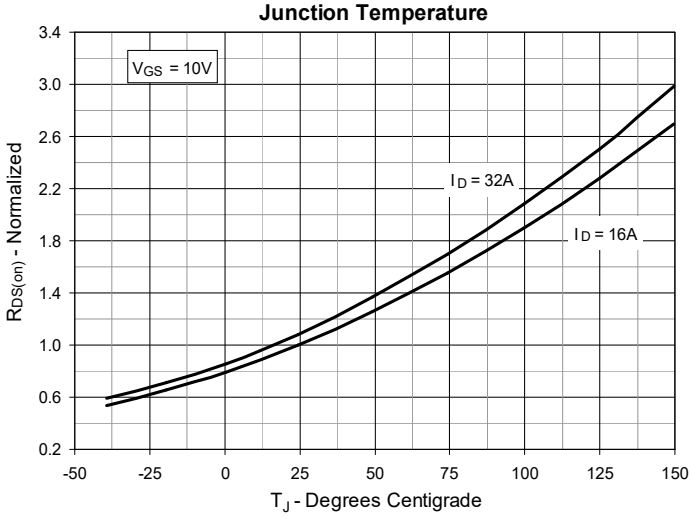


Fig. 5. $R_{DS(on)}$ Normalized to I_D = 16A Value vs. Drain Current

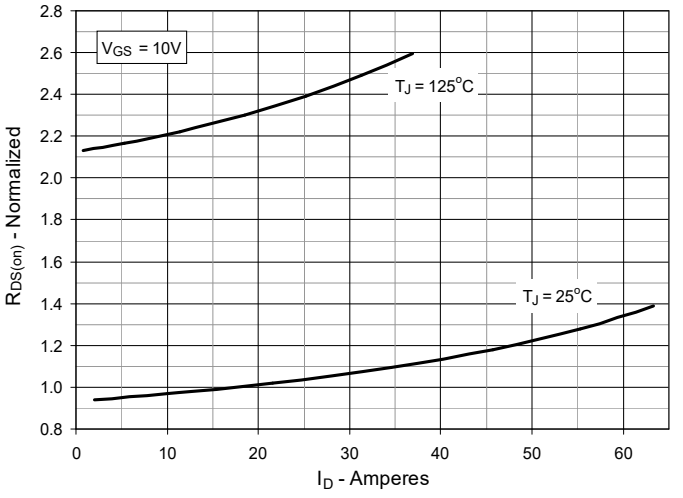
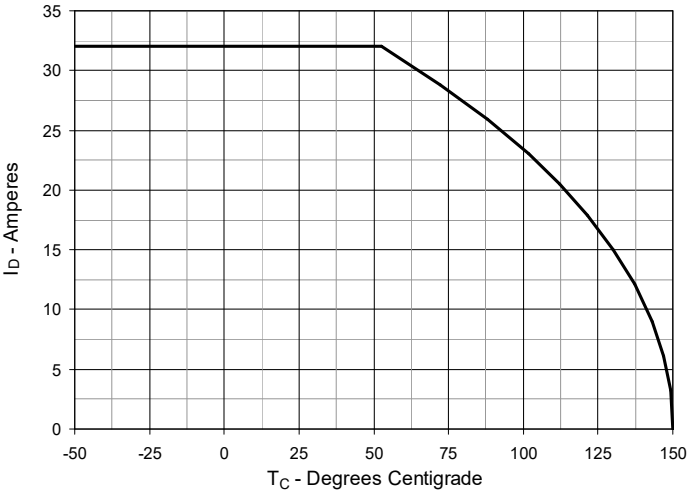


Fig. 6. Maximum Drain Current vs. Case Temperature



© 2020 IXYS CORPORATION, All Rights Reserved

Fig. 7. Input Admittance

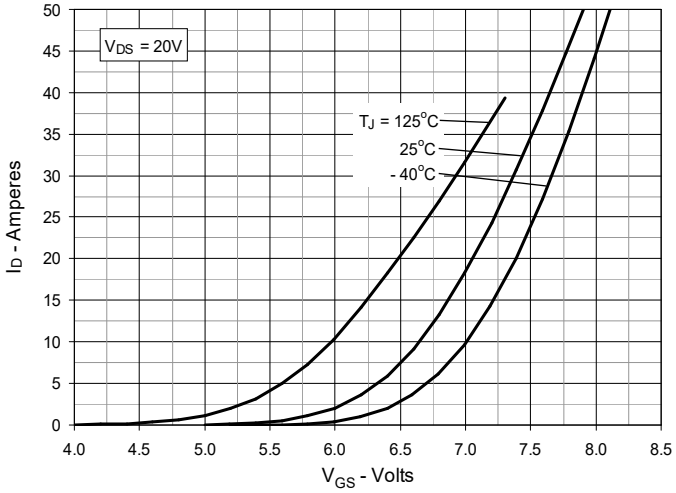


Fig. 8. Transconductance

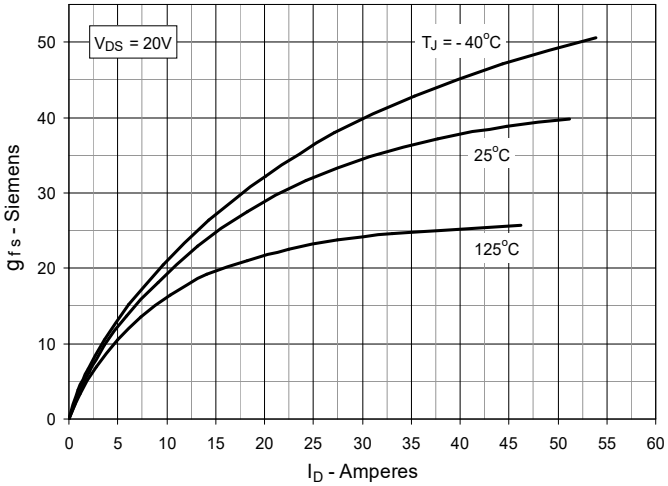


Fig. 9. Forward Voltage Drop of Intrinsic Diode

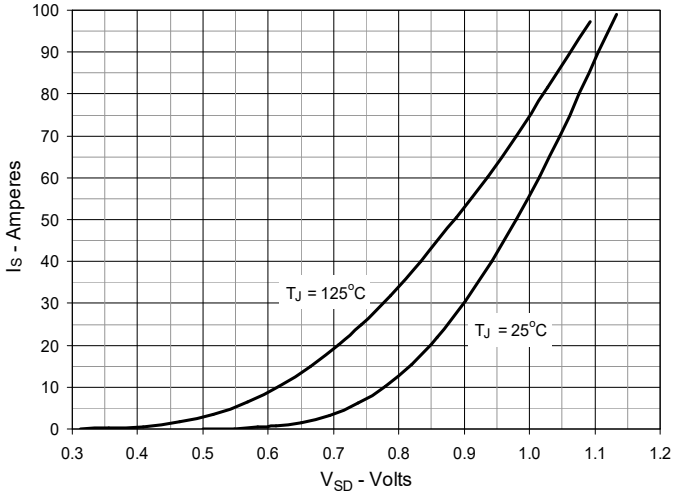


Fig. 10. Gate Charge

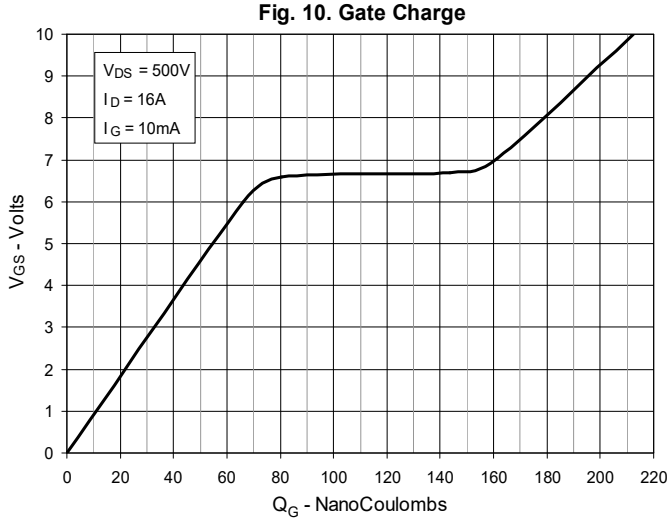


Fig. 11. Capacitance

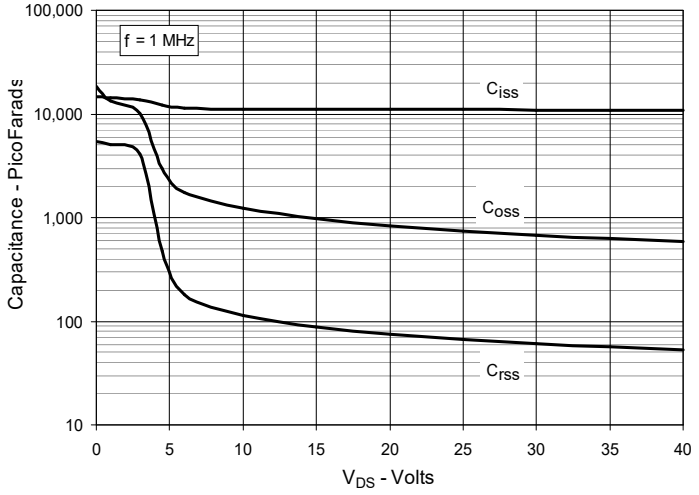
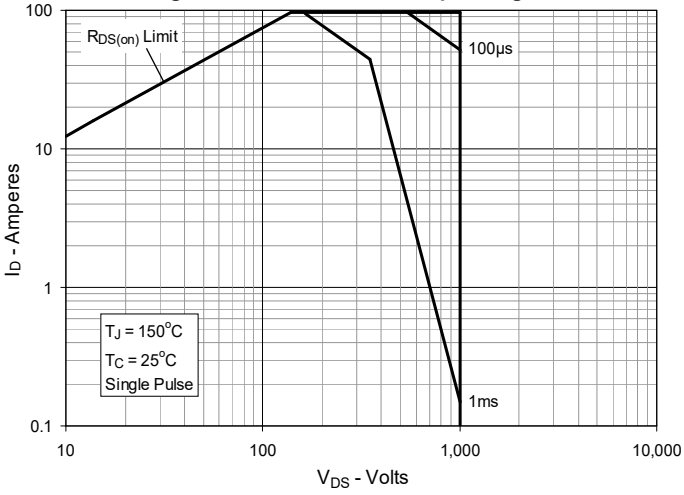
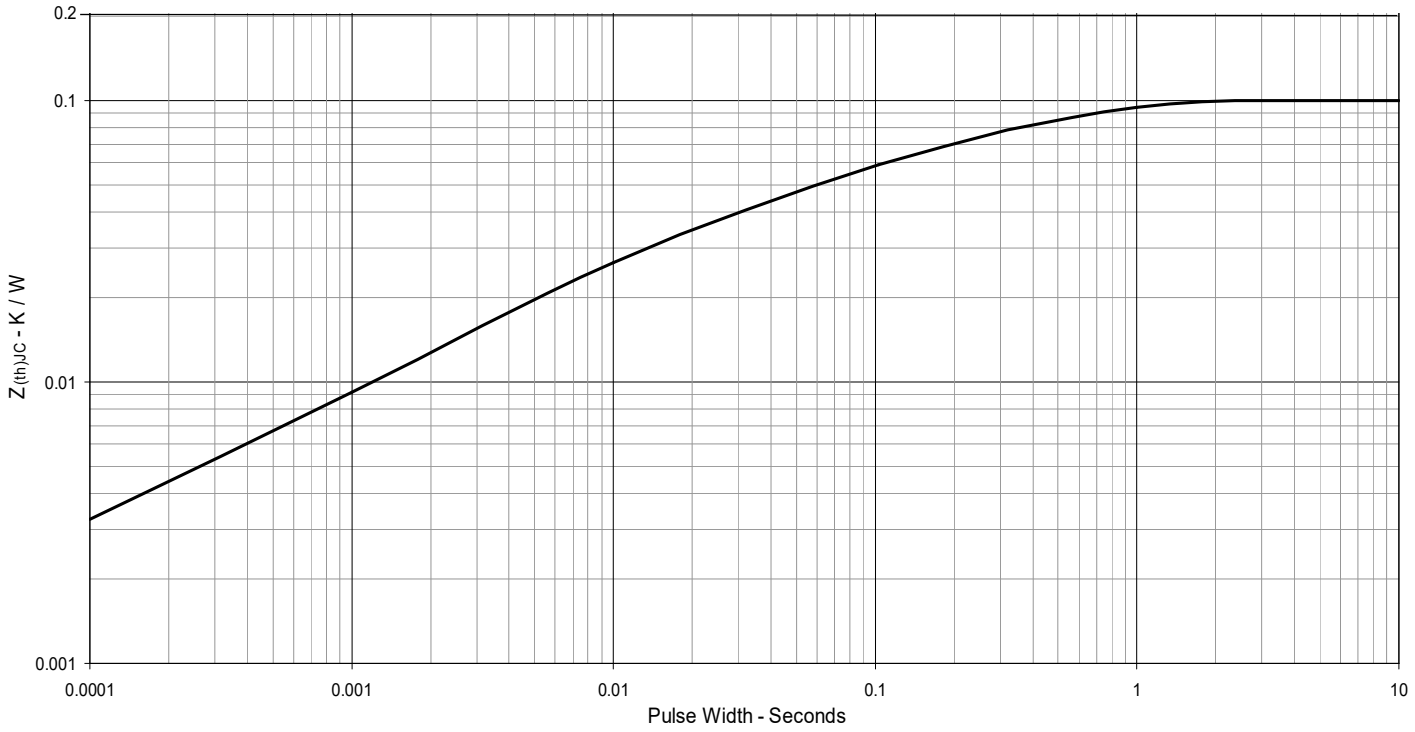


Fig. 12. Forward-Bias Safe Operating Area



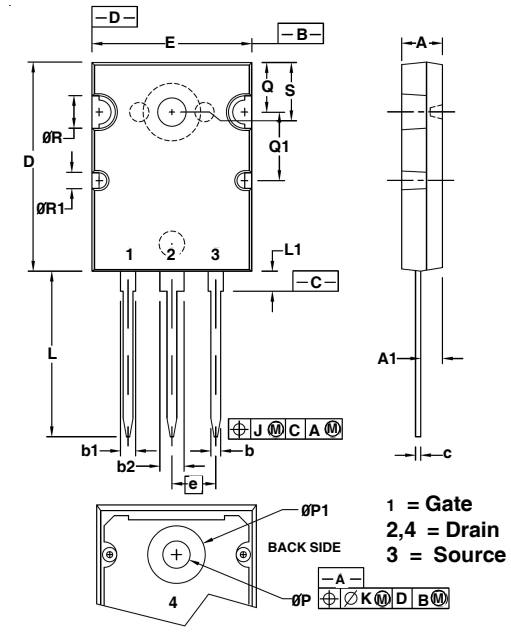
IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

Fig. 13. Maximum Transient Thermal Impedance



© 2020 IXYS CORPORATION, All Rights Reserved

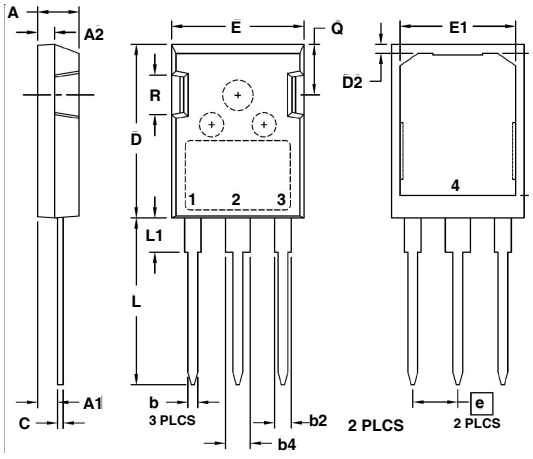
TO-264 Outline



1 = Gate
2,4 = Drain
3 = Source

SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.209	4.70	5.31
A1	.102	.118	2.59	3.00
b	.037	.055	0.94	1.40
b1	.087	.102	2.21	2.59
b2	.110	.126	2.79	3.20
c	.017	.029	0.43	0.74
D	1.007	1.047	25.58	26.59
E	.760	.799	19.30	20.29
e	.215BSC		5.46 BSC	
J	.000	.010	0.00	0.25
K	.000	.010	0.00	0.25
L	.779	.842	19.79	21.39
L1	.087	.102	2.21	2.59
øP	.122	.138	3.10	3.51
øP1	.270	.290	6.86	7.37
Q	.240	.256	6.10	6.50
Q1	.330	.346	8.38	8.79
øR	.155	.187	3.94	4.75
øR1	.085	.093	2.16	2.36
S	.243	.253	6.17	6.43

PLUS247™ Outline



1 = Gate
2,4 = Drain
3 = Source

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.190	.205	4.83	5.21
A1	.090	.100	2.29	2.54
A2	.075	.085	1.91	2.16
b	.045	.055	1.14	1.40
b2	.075	.087	1.91	2.20
b4	.115	.126	2.92	3.20
C	.024	.031	0.61	0.80
D	.819	.840	20.80	21.34
D1	.650	.690	16.51	17.53
D2	.035	.050	0.89	1.27
E	.620	.635	15.75	16.13
E1	.520	.560	13.08	14.22
e	.215 BSC		5.45 BSC	
L	.780	.810	19.81	20.57
L1	.150	.170	3.81	4.32
Q	.220	.244	5.59	6.20
R	.170	.190	4.32	4.83

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.



Disclaimer Notice - Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at www.littelfuse.com/disclaimer-electronics.

© 2020 IXYS CORPORATION, All Rights Reserved